VN1206B, VN1206D

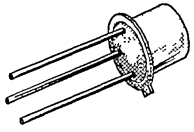
N-Channel Enhancement-Mode MOS Transistors

PRODUCT SUMMARY

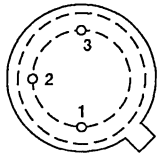
PART NUMBER	$V_{(BR)DSS}$ (V)	$r_{DS(ON)}$ (Ω)	I_D (A)	PACKAGE
VN1206B	120	6	0.59	TO-205AD
VN1206D	120	6	1.19	TO-220

Performance Curves: **VNDQ12** (See Section 7)

TO-205AD (TO-39)

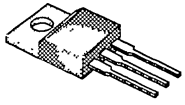


BOTTOM VIEW

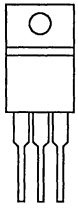


1 SOURCE
2 GATE
3 DRAIN & CASE

TO-220



TOP VIEW



1 2 3

1 GATE
2 & TAB – DRAIN
3 SOURCE

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)[2]

PARAMETERS/TEST CONDITIONS		SYMBOL	VN1206B	VN1206D	UNITS
Drain-Source Voltage		V_{DS}	120	120	V
Gate-Source Voltage		V_{GS}	±20	±30	
Continuous Drain Current	T_C = 25°C	I_D	0.59	1.19	A
	T_C = 100°C		0.37	0.75	
Pulsed Drain Current[1]		I_{DM}	2.5	2.5	
Power Dissipation	T_C = 25°C	P_D	5	20	W
	T_C = 100°C		2	8	
Operating Junction and Storage Temperature		T_j, T_{stg}	-55 to 150		°C
Lead Temperature (1/16" from case for 10 seconds)		T_L	300		

THERMAL RESISTANCE

THERMAL RESISTANCE	SYMBOL	VN1206B	VN1206D	UNITS
Junction-to-Case	R_{thJC}	25	6.25	°C/W

[1]Pulse width limited by maximum junction temperature
[2]Absolute maximum ratings have been revised from previous data sheet

ELECTRICAL CHARACTERISTICS[1]			LIMITS			
				VN1206		
PARAMETER	SYMBOL	TEST CONDITIONS	TYP[2]	MIN	MAX	UNIT
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 100 µA	145	120		V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 1 mA	1.4	0.8	2	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±15 V	±1		±100	nA
		T_C = 125°C	±5		±500	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 120 V, V_{GS} = 0 V	0.001		10	µA
		T_C = 125°C	0.5		500	µA
On-State Drain Current[3]	$I_{D(ON)}$	V_{DS} = 10 V, V_{GS} = 10 V	1.6	1		A
Drain-Source On-Resistance[3]	$r_{DS(ON)}$	V_{GS} = 2.5 V, I_D = 0.1 A	6		10	Ω
		V_{GS} = 10 V, I_D = 0.5 V	3.4		6	Ω
		T_C = 125°C	7		14.8	Ω
Forward Transconductance[3]	g_{FS}	V_{DS} = 10 V, I_D = 0.5 A	425	300		mS
Common Source Output Conductance[3]	g_{OS}	V_{DS} = 7.5 V, I_D = 0.1 A	400			µS
DYNAMIC						
Input Capacitance	C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz	35		125	pF
Output Capacitance	C_{oss}		15		50	pF
Reverse Transfer Capacitance	C_{rss}		2		20	pF
SWITCHING						
Turn-On Time	$t_{d(ON)}$	V_{DD} = 60 V, R_L = 150 Ω, I_D = 0.4 A, V_{GEN} = 10 V, R_G = 25 Ω (Switching time is essentially independent of operating temperature)	3		8	ns
	t_r		2.5		8	ns
Turn-Off Time	$t_{d(OFF)}$		7		18	ns
	t_f		2.5		12	ns

NOTES: 1. T_C = 25 °C unless otherwise noted.
2. For design aid only, not subject to production testing.
3. Pulse test; PW = 300 µs, duty cycle ≤ 2%.